

### 2.0x1.25mm INFRARED EMITTING DIODE

Part Number: KP-2012SF4C

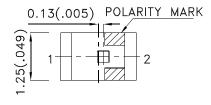
### **Features**

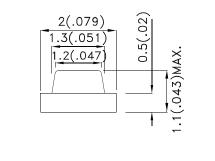
- 2.0mmx1.25mm SMT LED,1.1mm thickness.
- Mechanically and spectrally matched to the phototransistor.
- Package: 2000pcs / reel.
- Moisture sensitivity level : level 3.
- RoHS compliant.

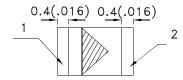
### Description

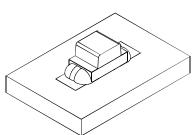
SF4 Made with Gallium Aluminum Arsenide Infrared Emitting diodes.

# **Package Dimensions**









- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is ±0.1(0.004") unless otherwise noted.
- 3. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

  4. The device has a single mounting surface. The device must be mounted according to the specifications.

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## **Selection Guide**

Part No.	Dice	Lens Type	Po (mW/sr) [2] @ 20mA		Viewing Angle [1]
			Min.	Тур.	201/2
KP-2012SF4C	SF4 (GaAlAs)	Water Clear	0.8	1.5	120°

### Notes:

- 1. 01/2 is the angle from optical centerline where the luminous intensity is 1/2 of the optical peak value. 2. Radiant Intensity/ luminous flux: +/-15%.
- 3. Radiant Intensity value is traceable to the CIE127-2007 compliant national standards.

## Electrical / Optical Characteristics at TA=25°C

Parameter	P/N	Symbol	Тур.	Max.	Units	Test Conditions	
Forward Voltage [1]	SF4	VF	1.3	1.6	V	IF=20mA	
Reverse Current	SF4	lr		10	uA	V <sub>R</sub> = 5V	
Capacitance	SF4	С	90		pF	VF=0V;f=1MHz	
Peak Spectral Wavelength	SF4	λP	880		nm	IF=20mA	
Spectral Bandwidth	SF4	Δλ1/2	50		nm	I=20mA	

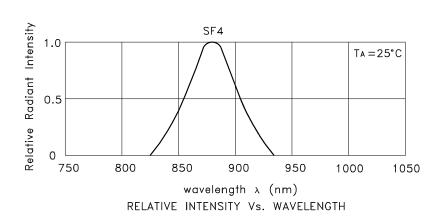
Forward Voltage: +/-0.1V.
 Wavelength value is traceable to the CIE127-2007 compliant national standards.

## Absolute Maximum Ratings at TA=25°C

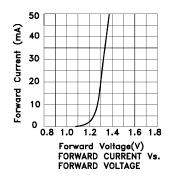
Parameter	Symbol	SF4	Units
Power dissipation	PD	80	mW
DC Forward Current	lF	50	mA
Peak Forward Current [1]	iFS	1.2	А
Reverse Voltage	VR	5	V
Operating Temperature	Та	-40 To +85	°C
Storage Temperature	Тѕтс	-40 To +85	°C

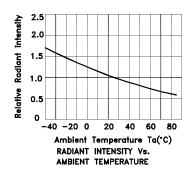
Note: 1. 1/100 Duty Cycle, 10µs Pulse Width.

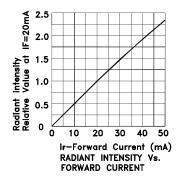
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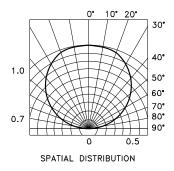


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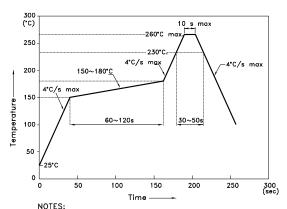
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### KP-2012SF4C

Reflow soldering is recommended and the soldering profile is shown below. Other soldering methods are not recommended as they might cause damage to the product.

Reflow Soldering Profile For Lead-free SMT Process.



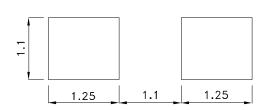
- NOTES:

  1.We recommend the reflow temperature 245°C(+/-5°C). The maximum soldering temperature should be limited to 260°C.

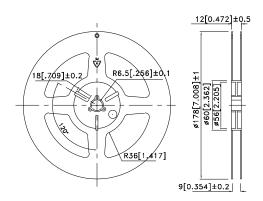
  2.Don't cause stress to the epoxy resin while it is exposed to high temperature. to high temperature.

  3.Number of reflow process shall be 2 times or less.

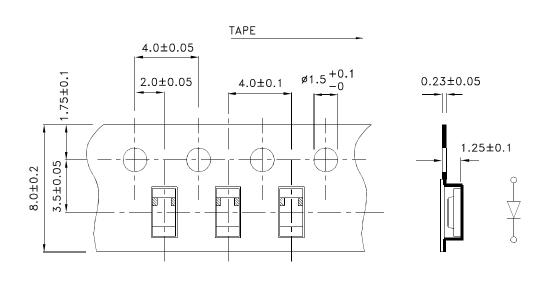
## **Recommended Soldering Pattern** (Units: mm; Tolerance: ± 0.1)



### **Reel Dimension**



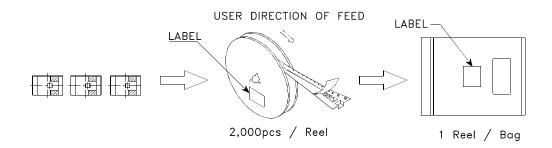
**Tape Specifications** (Units: mm)

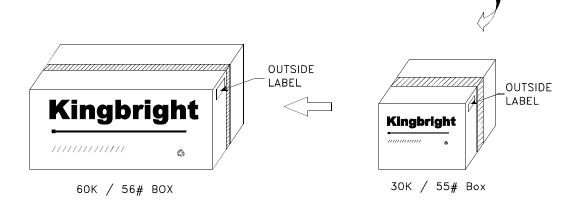


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## **PACKING & LABEL SPECIFICATIONS**

### KP-2012SF4C







Detailed application notes are listed on our website. http://www.kingbright.com/application\_notes

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